

# Progress with CdTe and high-flux CdZnTe XIDER detector prototypes

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The European Synchrotron



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## ✦ Introduction

- *2D X-ray detectors for scattering/diffraction applications at ESRF EBS*

## ✦ The XIDER project

- *Project overview and status*

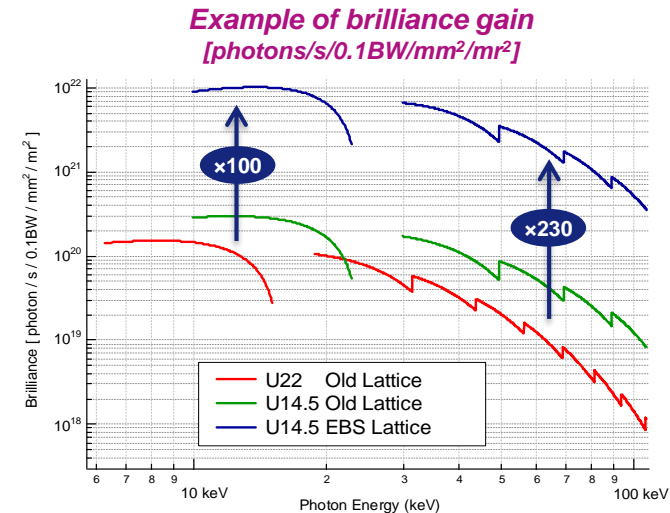
## ✦ CdTe and high-flux CZT XIDER assemblies

- *Direct photocurrent detection: time resolution capabilities*
- *Signal-induced leakage current: comparative measurements*

## ✦ Summary

## The ESRF upgraded storage ring: **Extreme Brilliant Source (EBS)**

- ▶ **New ring lattice: in user mode operation since 2020**
- ▶ **More photons in the sample: up more than  $10^{15}$  X-rays/sec**
  - **Higher brilliance** photon source: lower electron emittance ( $\times 30$ ), reduced gap undulators
  - Less divergent / more focused beams: **more efficient optics**
  - **Increased beam coherence**  $\rightarrow$  excellent for coherent scattering methods (ptychography, CDI, XPCS)
  - Many experimental techniques can move toward **higher X-ray energies**
- ▶ **New science opportunities require improved instrumentation**
  - X-ray detectors
    - ✓ **Extended dynamic range**
    - ✓ **Shorter time domains: intrinsic time resolution and frame rate**
    - ✓ **Detection of high energy photons**

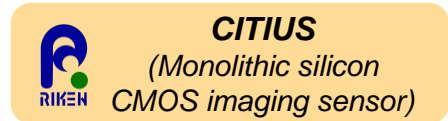
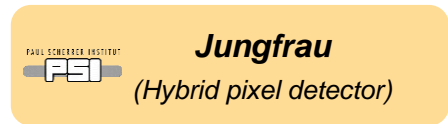


## ▶ We need detectors able to operate with higher photon fluxes and at high photon energies

- Current photon counting detectors are flux limited due to pulse pile-up: *few Mcps/pixel with acceptable losses*
- Moving from photon counting to charge integration readout with high-Z sensors (e.g. CdTe) would be the natural choice
  - *But the “conventional” charge integration readout scheme cannot be applied with continuous beams*
  - *Charge trapping in deep-level defects of the compound semiconductor*
    - *high value of the dark/leakage current*
    - *with “unpredictable” variations → **signal-induced leakage current** (also called afterglow, aftersignal, ...)*

## ▶ At ESRF we have started using/evaluating charge integrating systems

- Similar pixel pitch ~75  $\mu\text{m}$
- Very high photon flux (if very short integration intervals)
- Can be used at storage rings with continuous beams, but ...
  - *only at relatively low X-ray energies (silicon sensors)*
  - *must operate at their maximum frame rate to “slice” the integration time in the shortest possible sub intervals*
    - *complex and very demanding DAQ and computing infrastructure, regardless of the application requirements*



# ESRF APPROACH FOR HIGH-ENERGY 2D DETECTORS

- ▶ No obvious approach for high photon energies → investigate new readout concepts
- ▶ Two different R&D directions followed from ESRF:
  - Pushing photon rate capabilities of counting detectors → **SPHIRD** (small pixels)
  - Incremental digital integration → **XIDER** (highest dynamic range and time resolution)
- ▶ The XIDER project:
  - R&D collaboration: ESRF and University of Heidelberg
  - Reference application: **time resolved high energy diffraction** (material science)
  - **Charge integration hybrid pixel detector** with high-Z sensors
  - Able to work with **high energies** (30-100keV) and **high photon fluxes**
  - Operation with **continuous** and **pulsed** beams

*D. Magalhães talk  
Tuesday @ 11h20*

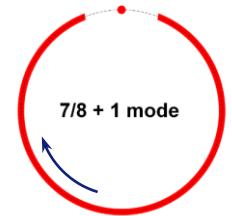


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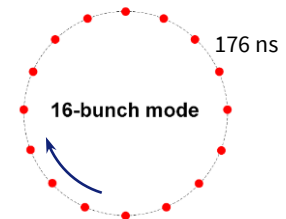
## Some target features/specifications :

- Sensor material: pixelated **CdTe** and **high-flux CZT**
- Configurable pixel pitch: **100  $\mu\text{m}$**  (physical) and **200  $\mu\text{m}$**  (2 $\times$ 2 binning)
- Dynamic range: from **single photon** sensitivity up to **10<sup>9</sup> X-ray/s/pixel**
- Readout ASIC:
  - Microelectronics technology node: **CMOS 65 nm**
  - Nearly 100% duty cycle, **deadtime free** readout
  - Burst mode up to **5.68 MHz** (ESRF 16-bunch repetition frequency)
  - In pixel **memory** (> 100 frames)
- Implementation and validation of the concept of **incremental digital integration**

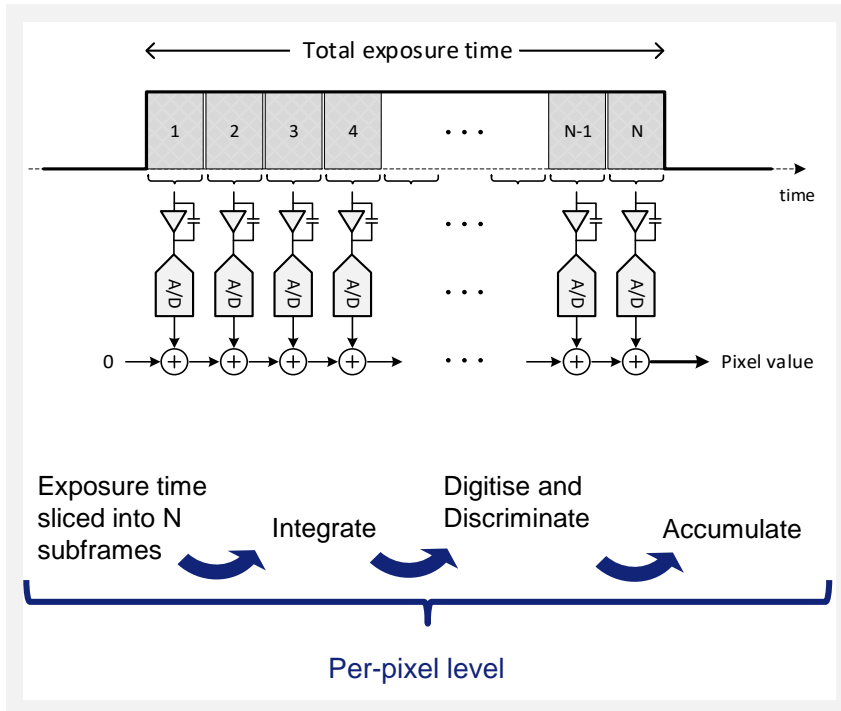
**Ccontinuous beam**  
(highest flux)



**Pulsed beam**  
(time resolved)



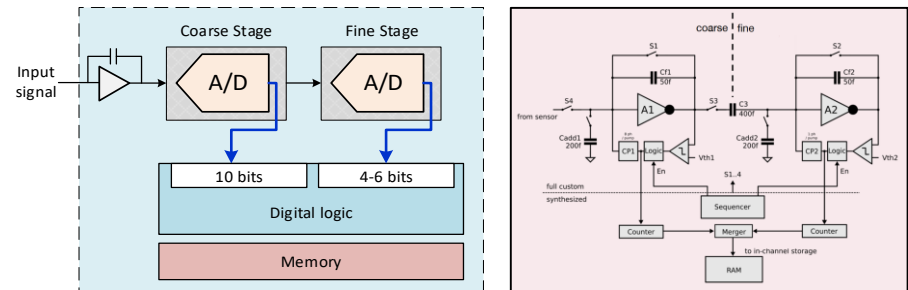
# INCREMENTAL DIGITAL INTEGRATION CONCEPT



## Incremental digital integration:

- Fine slicing (**subframes**) of the total integration interval (micro and sub-microsecond range)
- Noise and leakage contributions **partially suppressed** by signal thresholding/quantization
- **In-pixel ADC** → fully digital readout
- Possibility of **accumulation** of subframes and in-pixel **data storage**

## XIDER pixel



Incremental digital integration discussed in: *J. Inst.* **15** C01040  
<https://doi.org/10.1088/1748-0221/15/01/C01040>

Readout implementation discussed in: *J. Inst.* **16** P03023  
<https://doi.org/10.1088/1748-0221/16/03/P03023>

## The XIDyn collaboration

- Other labs have shown interest in some of the concepts proposed in XIDER
- **UKRI-STFC** and **Diamond Light Source** are working on **DynamiX**, a new generation of high-dynamic range 2D diffraction detectors for Diamond-II
- We have initiated a collaboration aiming at:
  - **Sharing experience** and know-how
  - Investigating the feasibility of a **single ASIC design** matching the application requirements of both Diamond-II and ESRF-EBS: This requires extending the initial target specifications of XIDER
  - Working on a **common platform** for the full detector systems: sensors, module construction, DAQ, firmware/software, ...
- **European XFEL** has recently joined as an observer



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T5

T6

## ASIC design:

The XIDER pixel functionality is **particularly complex**:

- ✓ Fast analog front-end
- ✓ In-pixel analog-to-digital conversion
- ✓ Digital logic, sequencer, multiple modes of operation
- ✓ Built-in memory
- ✗ Power hungry

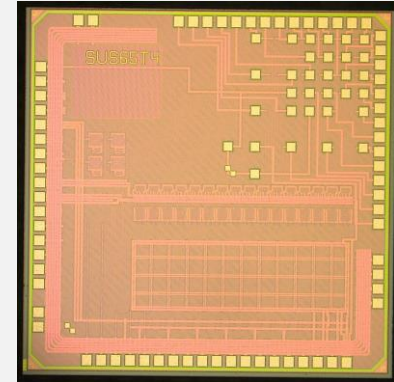
The pixel design has **progressed incrementally**:

- Six chips (T1 to T6) designed so far
- Not all the chips have used for X-ray testing
- Last X-ray measurements with T4: investigation at the pixel level

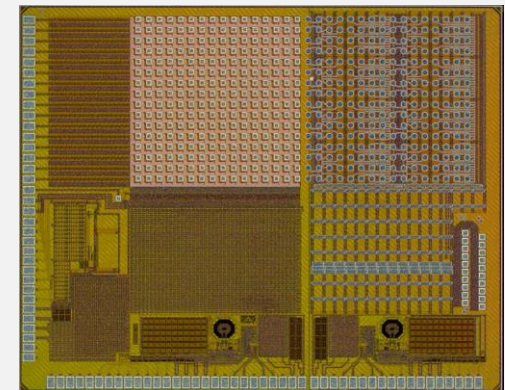
The last version (T6) includes a **16×16 pixel minimatrix**:

- Includes all the required functional blocks
- Includes **14 Gbps high-speed data** serializers from STFC
- Design directly **scalable to larger size** chips

## ASIC T4: 4×4 pixels



## ASIC T6: 16×16 pixels

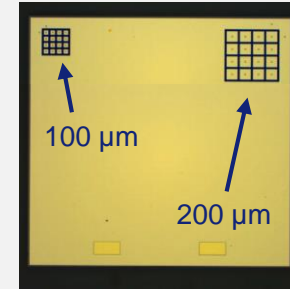


## Prototypes T4:

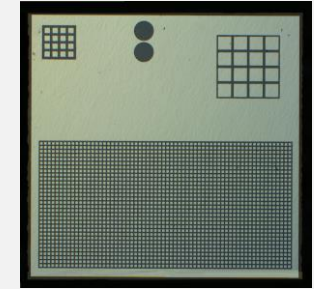
- 100  $\mu\text{m}$  and 200  $\mu\text{m}$  pixel pitch
- 4x4 pixel structures (in a 4x4 mm<sup>2</sup> total sensor size)
- 1 mm thick CdTe (ohmic contacts)
- 2 mm thick high-flux CZT

## Characterization:

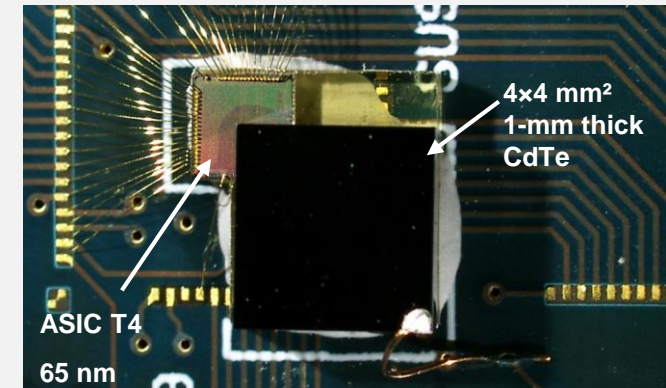
- The initial investigation work was done with CdTe assemblies
  - CdTe devices perform poorly (as anticipated) : instability and irreproducibility of dark/leakage current behaviour
- High-flux CZT assemblies available only very recently
- Measurements taken both with 30 keV X-rays at BM05/ESRF and with calibrated LED sources at the lab:
  - LED light (730 nm) reproduces in the laboratory a similar behaviour than observed with 30 keV X-rays at the beamline



**CdTe**  
(Acrorad)



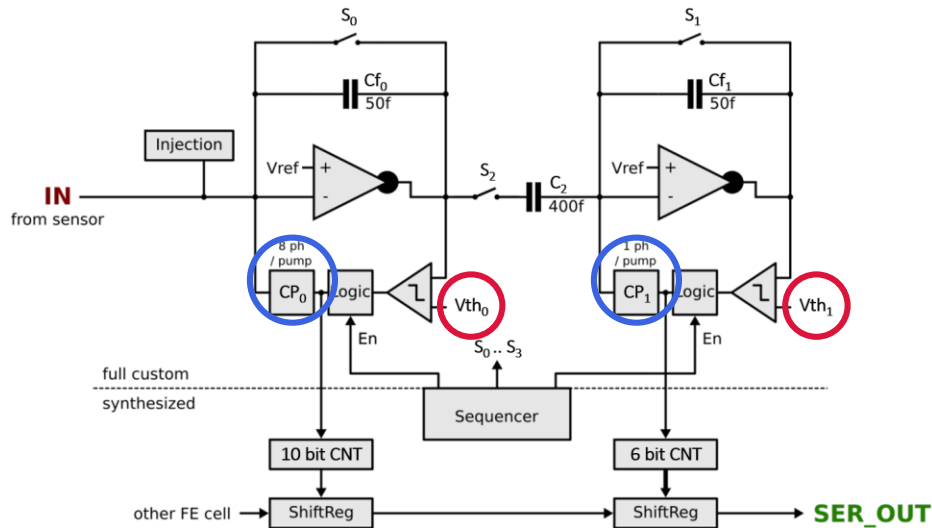
**High-flux CZT**  
(Redlen / Due2lab)



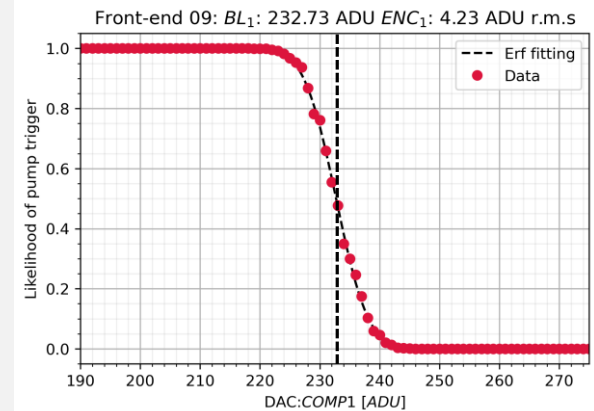
# CALIBRATION PROCEDURE

## Parameters to be calibrated:

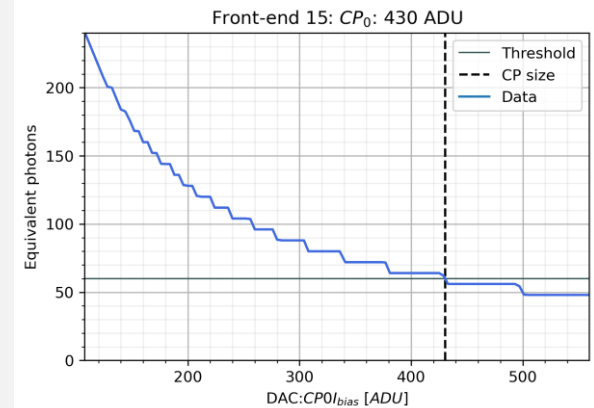
- Thresholds and charge pumps (×2)
- All trimmable with 10-bit DACs
- Using internal charge injection

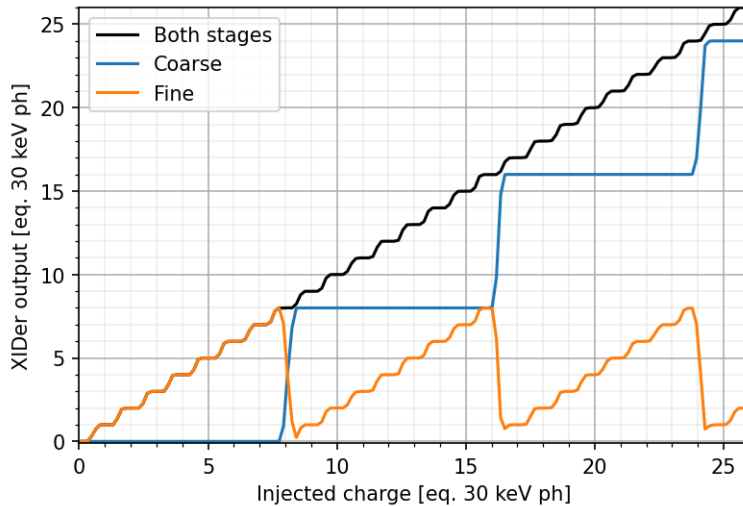


## Threshold calibration



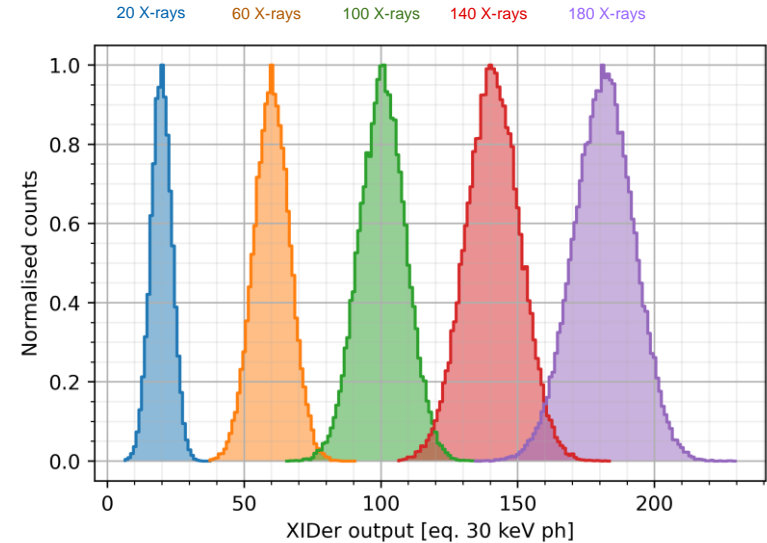
## Charge packet calibration





## Internal charge injector:

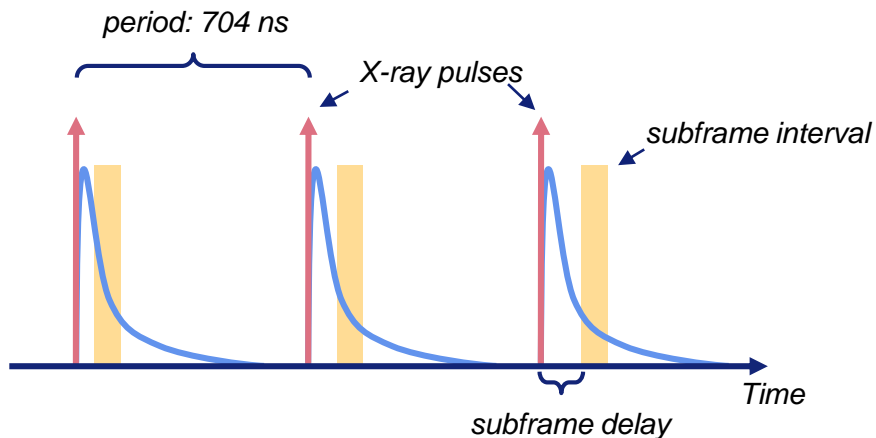
- Injection circuit: 10-bit DAC
- Mid-tread ADC response
- Electronic noise: 350 e<sup>-</sup> rms



## External electronic injection:

- External waveform generator
- Emulates Poisson statistics with Gaussian noise

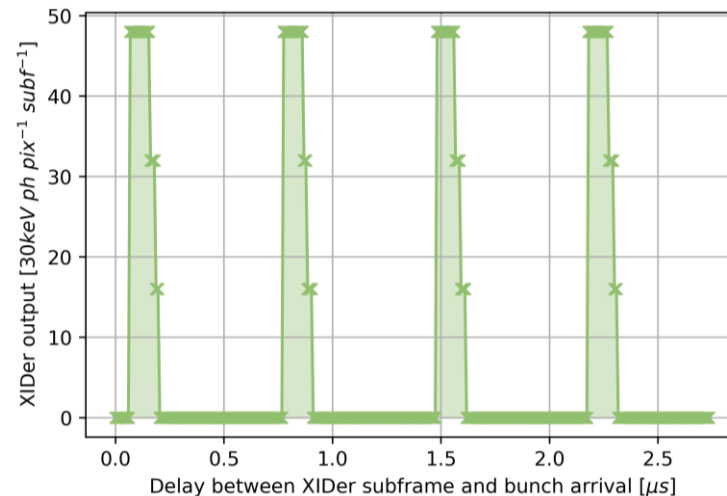
# DETECTION OF DIRECT PHOTOCURRENT: TIME-RESOLUTION



- XIDER active subframe of ~100 ns
- 4-bunch filling mode: 100 ps X-ray pulses every 704 ns
- Photon induced signal

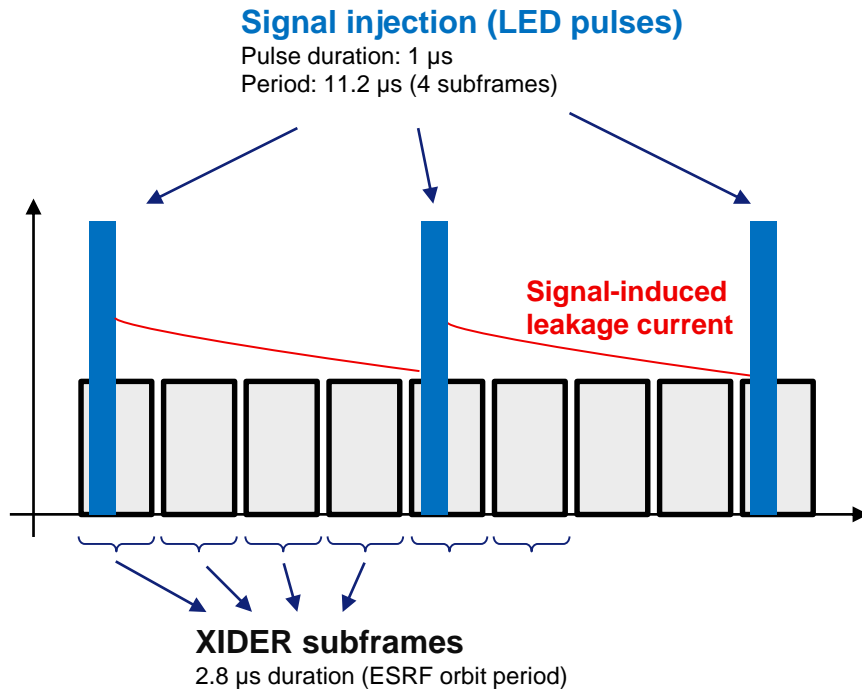
## Notes:

- Energy: 30 keV in 4-bunch filling mode
- XIDER subframes synchronous to the X-ray pulses
- Delay between X-ray pulses and the subframe start is changed
- Results are consistent with the collection of “direct photocurrent” in few 10s of nanoseconds



- Example of 4-bunch full orbit scan using a CdTe XIDER assembly
- Similar results with high flux CZT

# STUDYING THE SIGNAL-INDUCED LEAKAGE CURRENT



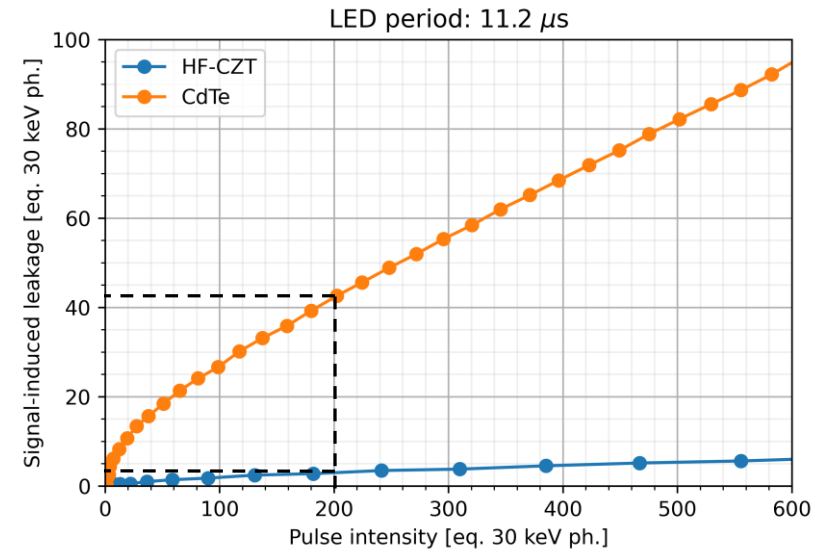
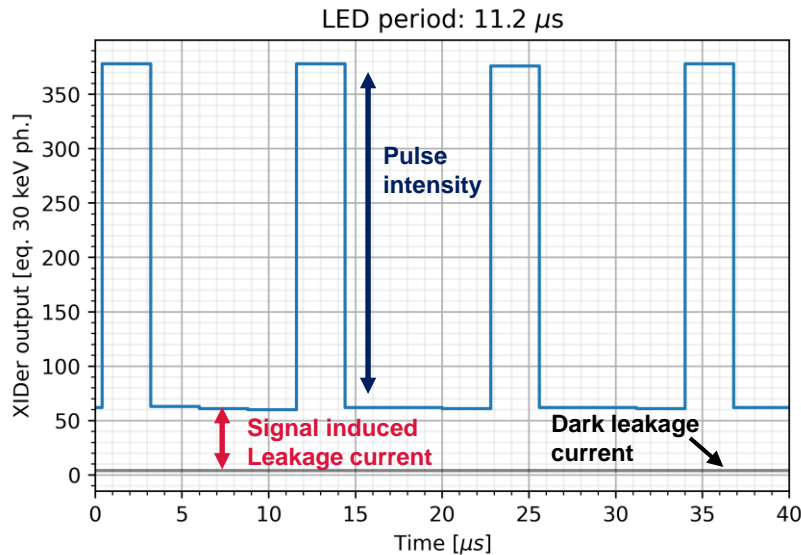
We use discontinuous (pulsed) illumination to separate the direct photocurrent (signal) from the signal-induced leakage current

## Measurement Setup:

- CdTe and CZT sensors:
  - cathode electrodes: <20 nm thick platinum
- Light pulses:
  - Used to emulate 'low-energy' X-rays
  - Duration: 1  $\mu\text{s}$ , repetition 4 subframes (11.2  $\mu\text{s}$ )
  - Tuneable intensity
  - Characterised with a silicon photodiode
- LED source:
  - $\lambda_{\text{LED}}$ : 730 nm (far red)
  - $E_{\text{gap, Cd(Zn)Te}}$ : 1.5 eV (830 nm)

# SIGNAL-INDUCED LEAKAGE CURRENT: STEADY-STATE MEASUREMENTS

**Objective:** to characterize the relation between pulse intensity (direct photocurrent) and leakage current induced by the pulsed illumination in **steady state** conditions



## Notes:

- Measurements in steady state conditions
  - CdTe: 2 mins of stabilization after illumination start
  - CZT: 15 seconds
- Dark leakage current (in absence of illumination) subtracted

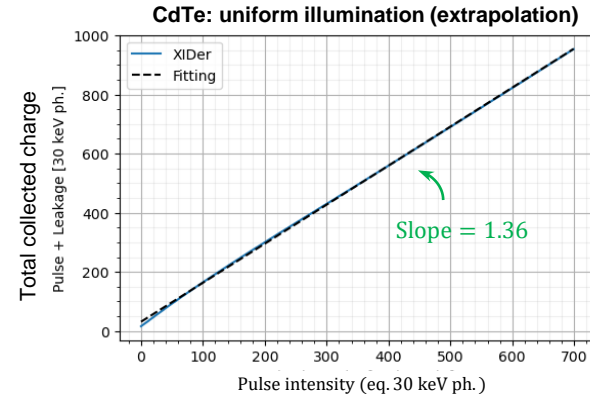
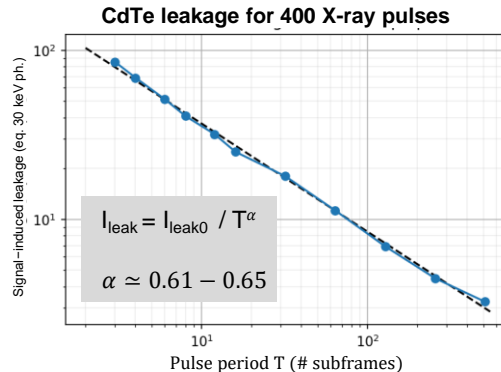
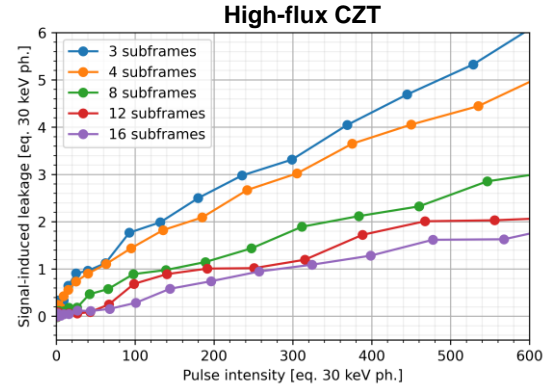
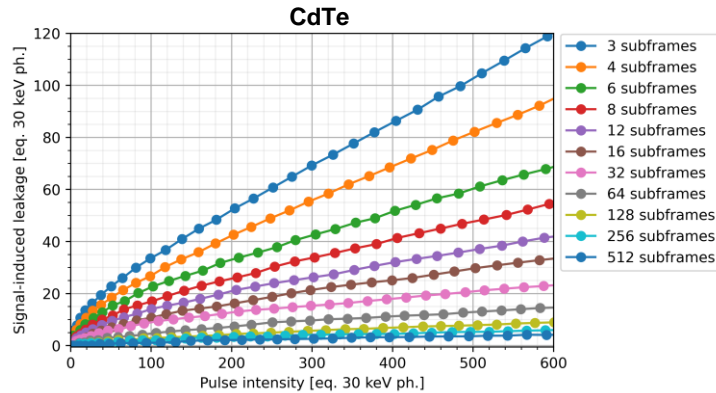
## Comparison of CZT and CdTe sensors:

- Leakage-to-pulse ratio as figure of merit:
  - CdTe: ~20% per subframe, ~80% integrated
  - CZT: ~1% per subframe, ~4% integrated

# SIGNAL-INDUCED LEAKAGE CURRENT: STEADY-STATE MEASUREMENTS

## Notes:

- The curves and the leakage-to-pulse ratio depends on the LED periodicity (integrated dose)
- The usual observation is confirmed: high flux CZT performs considerably better than CdTe



Preliminary results!

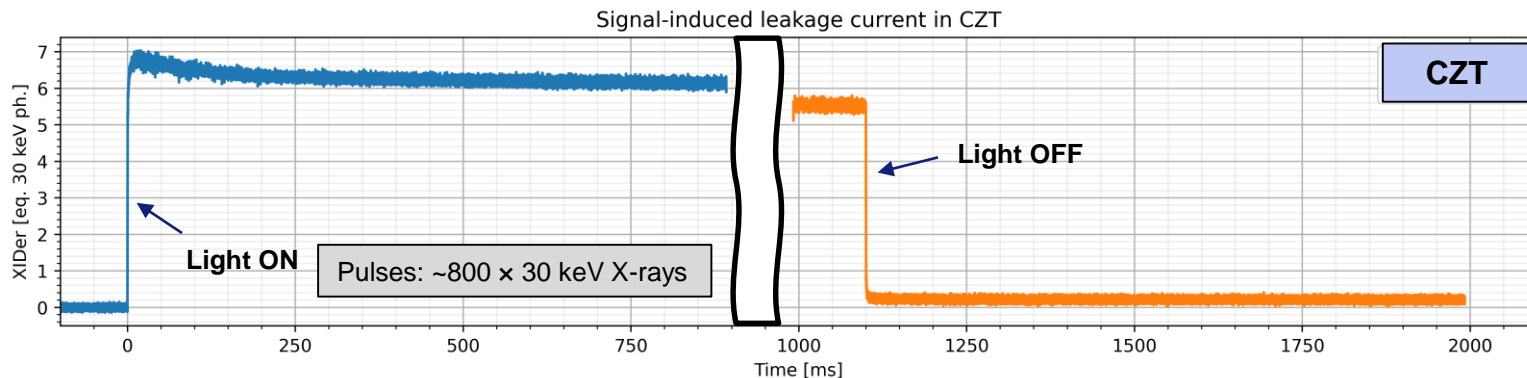
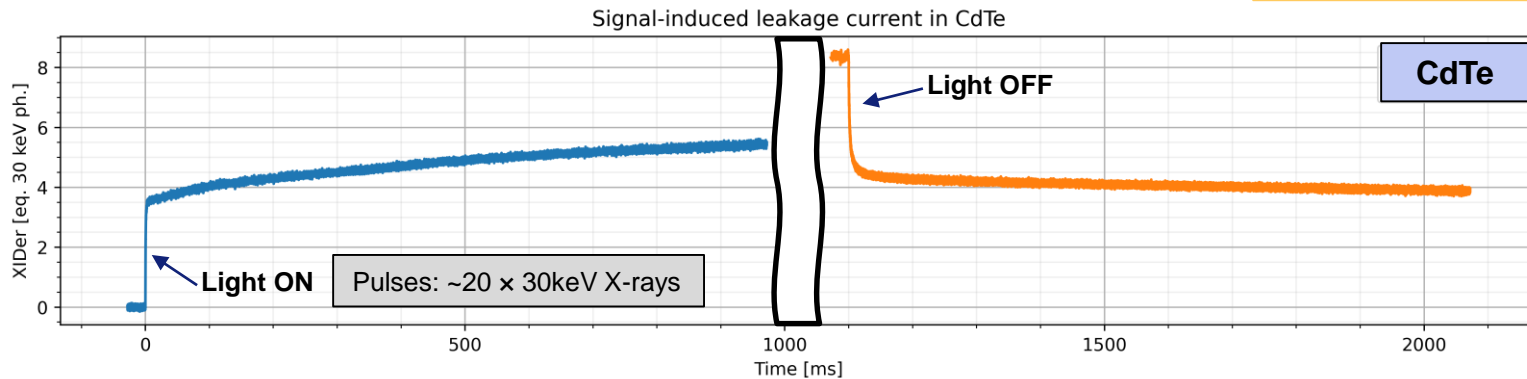
36% excess current !!



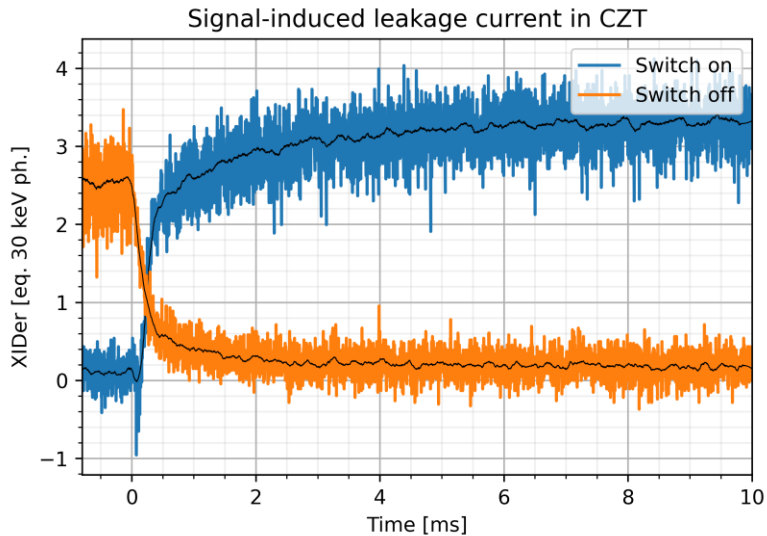
# SIGNAL-INDUCED LEAKAGE CURRENT: TRANSIENT RESPONSE

**Objective:** to characterize the evolution of the leakage current induced by the pulsed illumination in transient conditions by switching ON and OFF the periodic pulsed illumination

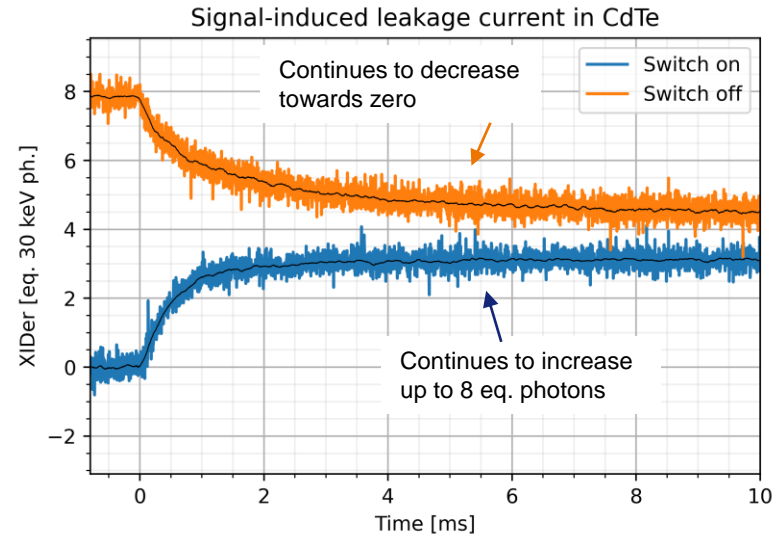
ON/OFF interval: 5 minutes



## Comparison of CZT and CdTe sensors (Data are dark current corrected)



**CZT:** steady state is reached (90%) in less than 5ms



**CdTe:** it takes seconds/minutes to approach steady state

- ▶ **Building charge integrating hybrid pixel detectors with high-Z sensors is challenging**
  - The major issue is the variation of leakage/dark current induced by X-ray irradiation
- ▶ **But a crucial matter for high-energy high-brilliance synchrotrons such as ESRF-EBS**
  - The XIDER project is our approach to address this problem
  - Potentially of interest for other applications and/or facilities (e.g. the XIDyn collaboration)
- ▶ **XIDER is also a tool to explore the response of CdTe and high-flux CZTs In micro and sub-microsecond time scales**
  - Direct photocurrent is collected in few tens of nanoseconds
  - But the irradiation induced leakage/dark current variations are substantial at high X-ray fluxes
  - Our initial measurements confirm that high-flux CZT performs much better than CdTe:
    - ✓ *In terms of leakage amplitude variations: about 40 times smaller*
    - ✓ *In terms of time response: milliseconds vs seconds/minutes*
- ▶ **We are starting the evaluation of pixelated CZT with XIDER. We plan to complete/continue the study:**
  - Linearity of the photocurrent component, response under different illumination patterns/conditions
  - Response at higher X-ray energies (up to 100keV)
  - Temperature dependence
  - ...

THANK YOU FOR YOUR ATTENTION



<https://indico.esrf.fr/event/18/>

- [HiZPAD webinars](#) were established during the pandemic by scientists from several light sources
- A forum dedicated to the discussion of [high-Z sensors](#) and associated technology
- [In-person](#) meeting at DESY - [Sept. 20-21st](#)
- Hybrid meeting ([no registration fees](#))
- Plenty of time for [open discussions](#)
- [Young researchers](#) are encouraged to present and discuss their results



## HiZPAD workshop - HAMBURG

Sep 20 – 21, 2023  
CFEL, DESY CAMPUS, HAMBURG  
Europe/Paris time zone

Enter your search term

### Overview


[Timetable](#)

[Registration](#)

[Participant List](#)

### Contact

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 +33476882111

As the use of High-Z detectors becomes more prevalent to meet the challenging needs of the photon science community (higher photon energy, fluxes, frame rates...), this workshop aims to provide a forum that fosters discussion between scientists in the field.

Although you are highly encouraged to come discuss in person, this meeting can be followed remotely.

**The deadline for registration is June 31st.** Timetable and joining instructions will be communicated upon registration.

You're welcome to volunteer for a talk!

### GENERAL TOPICS:

- (High-Z) Detector Developments
- High-Z sensors: contacts, interconnects and material characterization
- Applications of high-Z detectors in Photonic Science

### ADDITIONAL EVENTS:

- **Sept. 20th: Workshop Dinner**
- **Sept. 21st: Scientific Brunch** | An opportunity to showcase your work (poster) over an informal brunch
- **Sept. 21st: Capability Showcase** | As a community we developed a framework of material characterization expertise, which we would map during this showcase! Experts are encouraged to present their developed capabilities, to foster information crossing and future inter-institutes collaborating work.

Participants are only expected to finance their travels and accommodation.

